

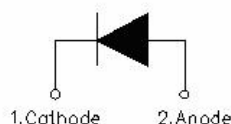
SDURF30Q60 ULTRAFAST RECTIFIER



Applications

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	600	V
Average Rectified Forward Current	$I_F (AV)$	50% duty cycle @Tc=70°C, rectangular wave form	30	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3ms, Half Sine pulse	200	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 30A, Pulse, $T_J = 25^{\circ}\text{C}$	1.56	1.80	V
	V_{F2}	@ 30A, Pulse, $T_J = 125^{\circ}\text{C}$	1.40	1.60	V
	V_{F3}	@ 30A, Pulse, $T_J = 150^{\circ}\text{C}$	1.34	-	V
Reverse Current*	I_{R1}	@ $V_R = \text{rated } V_R, T_J = 25^{\circ}\text{C}$	0.02	10	μA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 125^{\circ}\text{C}$	0.006	1	mA
	I_{R2}	@ $V_R = \text{rated } V_R, T_J = 150^{\circ}\text{C}$	0.025	-	mA
Reverse Recovery Time	t_{rr}	$I_F = 500\text{mA}, I_R = 1\text{A}, \text{ and } I_{rm} = 250\text{mA}, T_J = 25^{\circ}\text{C}$	32	40	ns
Reverse Recovery Time	t_{rr}	$I_F = 30\text{A}, diF/dt = -200\text{A}/\mu\text{s}$ $V_R = 400\text{V}, T_J = 25^{\circ}\text{C}$	78	-	ns
Reverse Recovery Charge	Q_{rr}		94	-	nC
Reverse Recovery Current	I_{RRM}		2.4	-	A
Reverse Recovery Time	t_{rr}	$I_F = 30\text{A}, diF/dt = -200\text{A}/\mu\text{s}$ $V_R = 400\text{V}, T_J = 125^{\circ}\text{C}$	136	-	ns
Reverse Recovery Charge	Q_{rr}		435	-	nC
Reverse Recovery Current	I_{RRM}		6.4	-	A
Reverse Recovery Time	t_{rr}	$I_F = 1\text{A}, diF/dt = -100\text{A}/\mu\text{s}$ $V_R = 30\text{V}, T_J = 25^{\circ}\text{C}$	30	-	ns
Reverse Recovery Charge	Q_{rr}		26	-	nC
Reverse Recovery Current	I_{RRM}		2	-	A
Reverse Recovery Time	t_{rr}	$I_F = 1\text{A}, diF/dt = -100\text{A}/\mu\text{s}$ $V_R = 30\text{V}, T_J = 125^{\circ}\text{C}$	65	-	ns
Reverse Recovery Charge	Q_{rr}		121	-	nC
Reverse Recovery Current	I_{RRM}		4	-	A

* Pulse width < 300 μs , duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	4.2	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	1.6	g
Case Style	ITO-220AC			

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

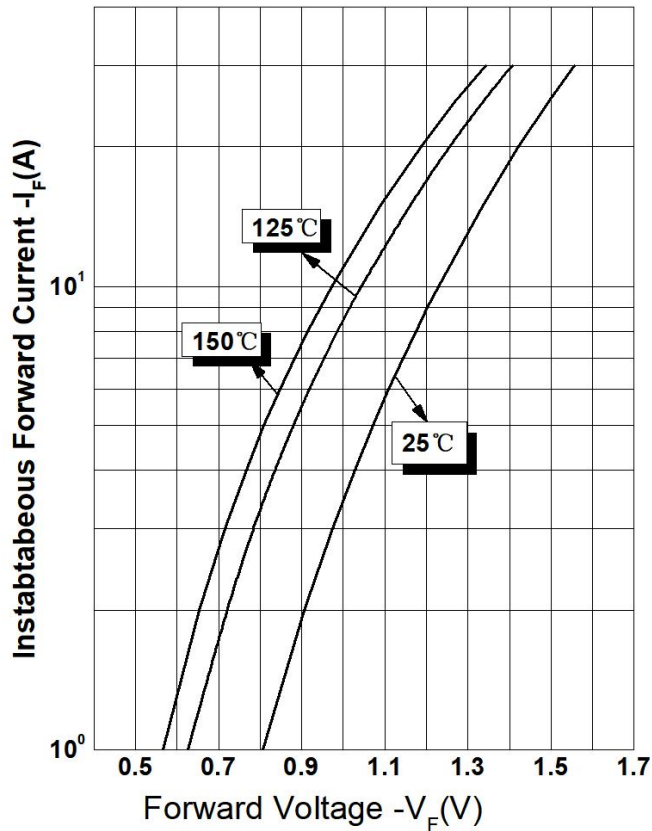


Figure 2
Typical Reverse Characteristics

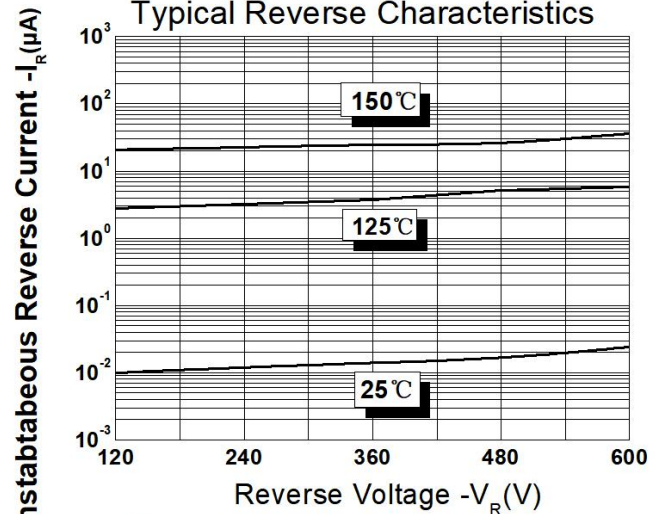
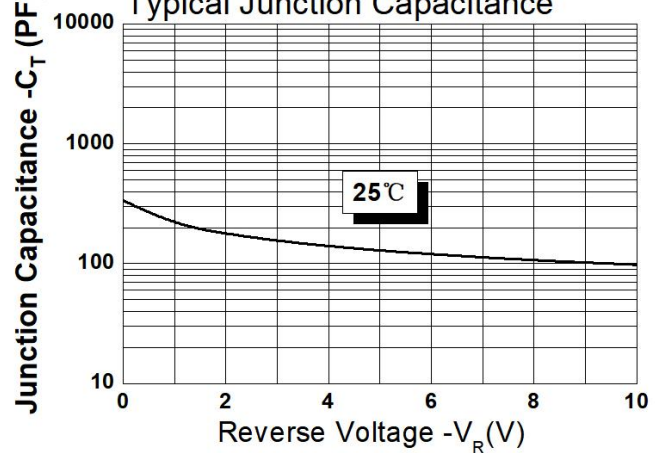


Figure 3
Typical Junction Capacitance



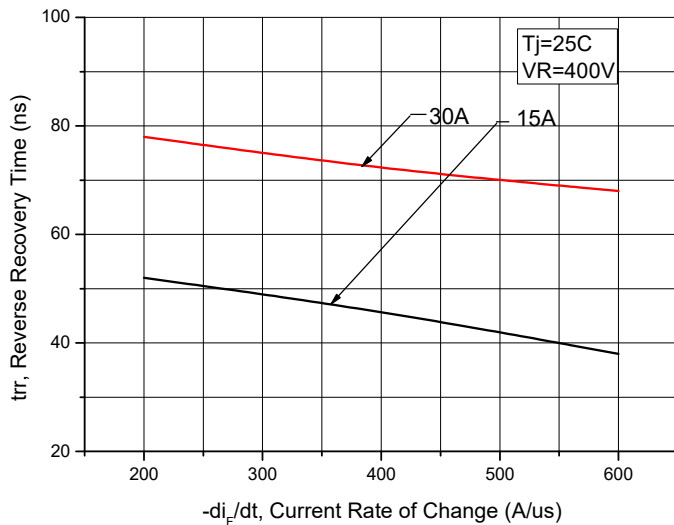


Figure 4. Reverse Recovery Time vs. Current Rate of Change

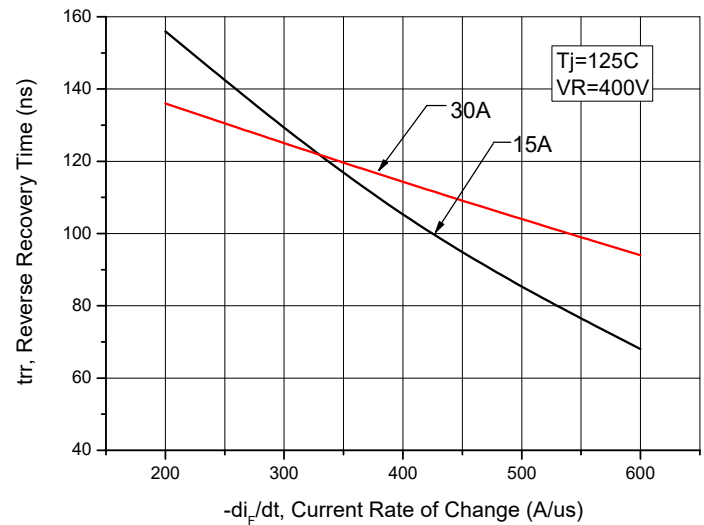


Figure 5. Reverse Recovery Time vs. Current Rate of Change

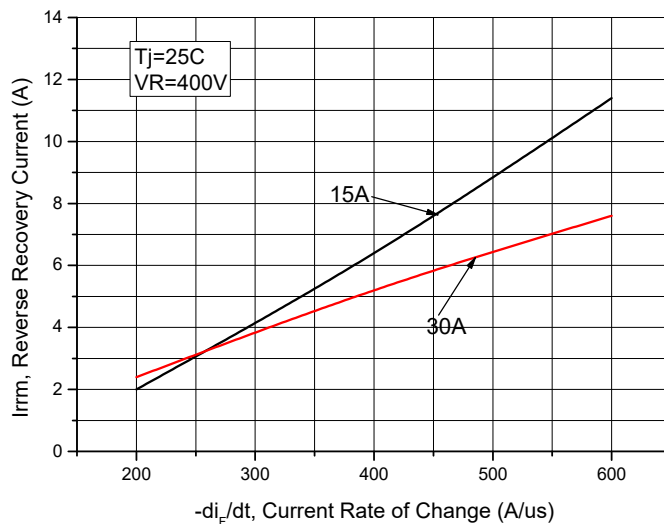


Figure 6. Reverse Recovery Current vs. Current Rate of Change

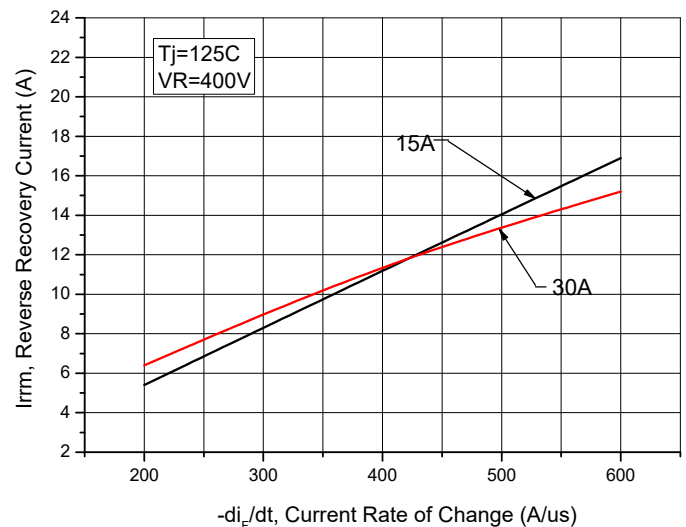


Figure 7. Reverse Recovery Current vs. Current Rate of Change

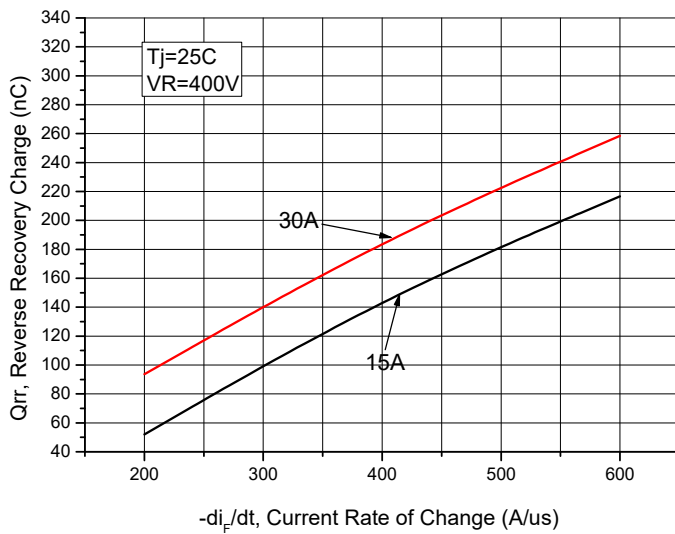


Figure 8. Reverse Recovery Charge vs. Current Rate of Change

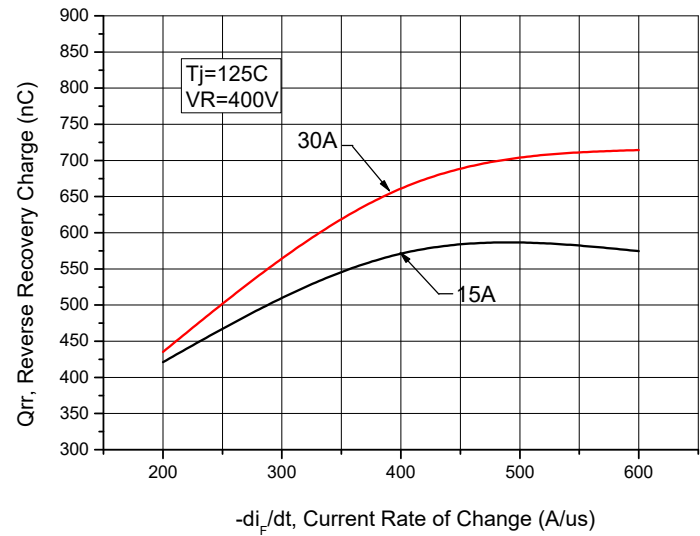


Figure 9. Reverse Recovery Charge vs. Current Rate of Change

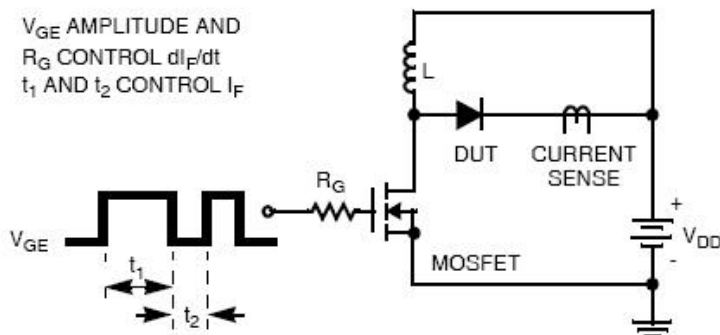


Figure 10. Diode Test Circuit

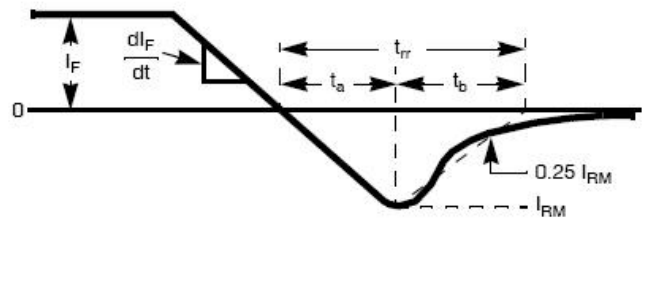
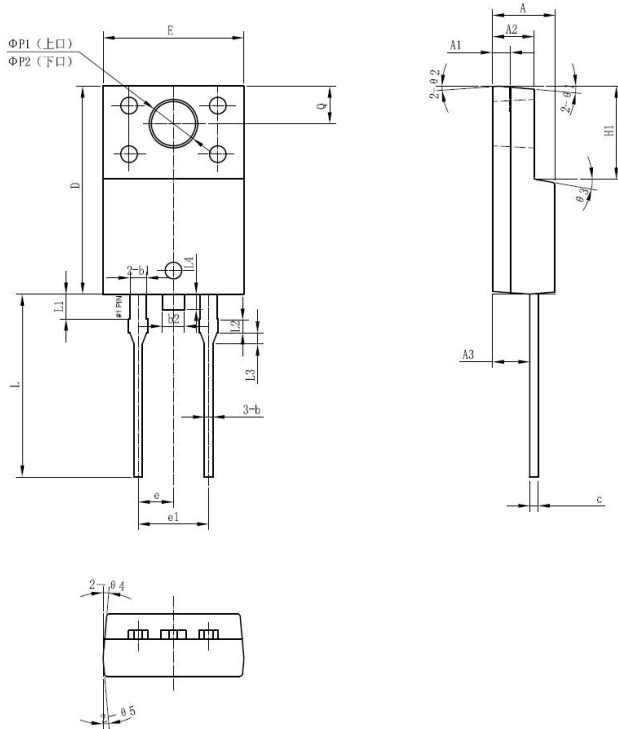


Figure 11. Diode Reverse Recovery Waveform

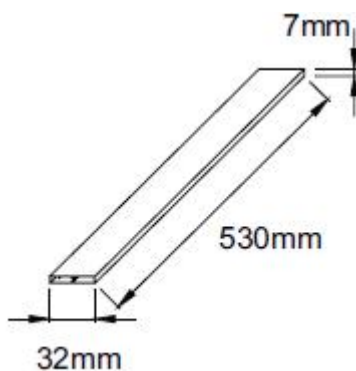
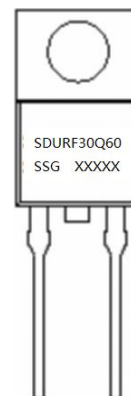
Mechanical Dimensions ITO-220AC


SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.30	4.50	4.70
A1	1.10	1.30	1.50
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
b	0.50	0.60	0.75
b1	1.10	1.20	1.35
b2	1.50	1.60	1.75
c	0.50	0.60	0.75
D	14.80	15.00	15.20
E	9.96	10.16	10.36
e	-	2.55	-
e1	5.00	5.10	5.16
H1	6.50	6.70	6.90
L	12.70	13.20	13.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
L4	-	1.10	1.50
ΦP1(上□)	3.30	3.50	3.70
ΦP2(下□)	2.99	3.19	3.39
Q	2.50	2.70	2.90
Θ1		5°	
Θ2		4°	
Θ3		10°	
Θ4		5°	
Θ5		5°	

Ordering Information:

Device	Package	Shipping
SDURF30Q60	ITO-220AC (Pb-Free)	50 pcs/ tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Tube Specification

Marking Diagram


Where XXXXX is YYWWL

SDUR = Device Type
 F = Package type
 30 = Forward Current (30A)
 Q = Q
 60 = Reverse Voltage (600V)
 SSG = SSG
 YY = Year
 WW = Week
 L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Technical Data
Data Sheet N2155 Rev. B



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